

Features

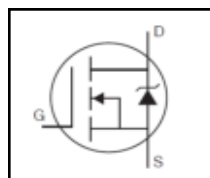
- Logic Level Gate Drive
- Ultra Low On-Resistance
- Surface Mount (IRLR3410)
- Straight Lead (IRLU3410)
- Advances Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

Description

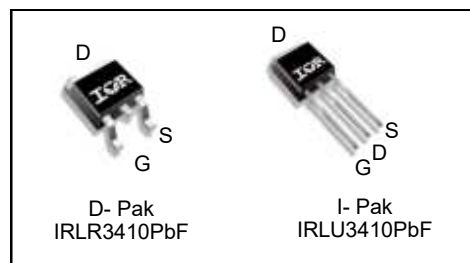
Fifth Generation HEXFET® Power MOSFET utilize advanced processing techniques to achieve the lowest possible on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient device for use in a wide variety of applications.

The D-PAK is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.

HEXFET® Power MOSFET



V_{DS}	100V
$R_{DS(on)}$	0.105Ω
I_D	17A



G	D	S
Gate	Drain	Source

Base part number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRLU3410PbF	I-Pak	Tube	75	IRLU3410PbF
IRLR3410PbF	D-Pak	Tube	75	IRLR3410PbF
		Tape and Reel	2000	IRLR3410TRLPbF

Absolute Maximum Ratings

Symbol	Parameter	Max.	Units
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	17	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	12	
I_{DM}	Pulsed Drain Current ①⑤	60	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	79	W
	Linear Derating Factor	0.53	W/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy ②⑤	150	mJ
I_{AR}	Avalanche Current ①⑤	9.0	A
E_{AR}	Repetitive Avalanche Energy ⑤	7.9	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.0	
T_J	Operating Junction and	-55 to + 175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 seconds (1.6mm from case)		

Thermal Resistance

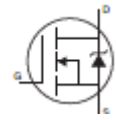
Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.9	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB Mount) ②	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	100	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.122	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	0.105	Ω	$V_{GS} = 10V, I_D = 10A$ ④
		—	—	0.125		$V_{GS} = 5.0V, I_D = 10A$ ④
		—	—	0.155		$V_{GS} = 4.0V, I_D = 9.0A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	1.0	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
g_{fs}	Forward Trans conductance	7.7	—	—	S	$V_{DS} = 25V, I_D = 9.0A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	$V_{DS} = 100V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 80V, V_{GS} = 0V, T_J = 150^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 16V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -16V$
Q_g	Total Gate Charge	—	—	34	nC	$I_D = 9.0A$
Q_{gs}	Gate-to-Source Charge	—	—	4.8		$V_{DS} = 80V$
Q_{gd}	Gate-to-Drain ('Miller') Charge	—	—	20		$V_{GS} = 5.0V$, See Fig. 6 and 13 ④⑤
$t_{d(on)}$	Turn-On Delay Time	—	7.2	—	ns	$V_{DD} = 50V$
t_r	Rise Time	—	53	—		$I_D = 9.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	30	—		$R_G = 6.0\Omega, V_{GS} = 5.0V$
t_f	Fall Time	—	26	—		$R_D = 5.5\Omega$, See Fig. 10 ④⑤
L_D	Internal Drain Inductance	—	4.5	—	nH	Between lead, ⑥ 6mm (0.25in.)
L_S	Internal Source Inductance	—	7.5	—		from package and center of die contact
C_{iss}	Input Capacitance	—	800	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	160	—		$V_{DS} = 25V$
C_{rss}	Reverse Transfer Capacitance	—	90	—		$f = 1.0\text{MHz}$, Fig. 5 ⑤



Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	17	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	60		
V_{SD}	Diode Forward Voltage	—	—	1.3	V	$T_J = 25^\circ\text{C}, I_S = 9.0A, V_{GS} = 0V$ ④
t_{rr}	Reverse Recovery Time	—	140	210	ns	$T_J = 25^\circ\text{C}, I_F = 9.0A$
Q_{rr}	Reverse Recovery Charge	—	740	1100	nC	$di/dt = 100A/\mu s$ ④⑤
t_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11).
- ② $V_{DD} = 25V$, starting $T_J = 25^\circ\text{C}$, $L = 3.1\text{mH}$, $R_G = 25\Omega$, $I_{AS} = 9.0A$. (See fig. 12).
- ③ $I_{SD} \leq 9.0A, di/dt \leq 540A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 175^\circ\text{C}$
- ④ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.
- ⑤ Uses IRL530N data and test conditions.
- ⑥ This is applied for I-PAK, L_S of D-PAK is measured between lead and center of die contact.
- ⑦ When mounted on 1" square PCB (FR-4 or G-10 Material). For recommended footprint and soldering techniques refer to application note #AN-994.

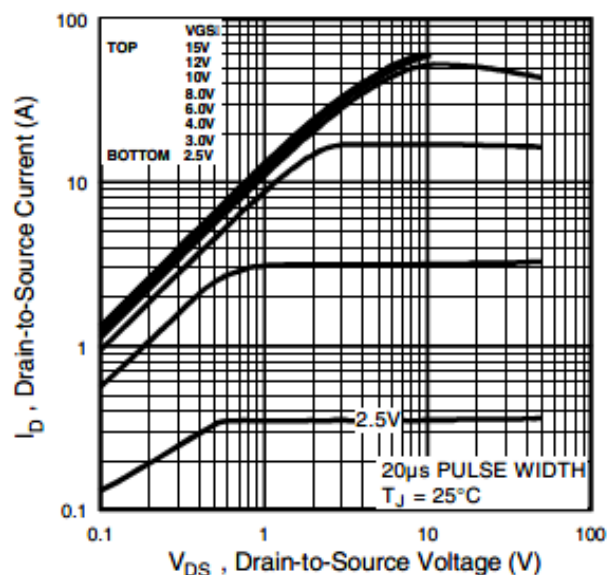


Fig. 1 Typical Output Characteristics

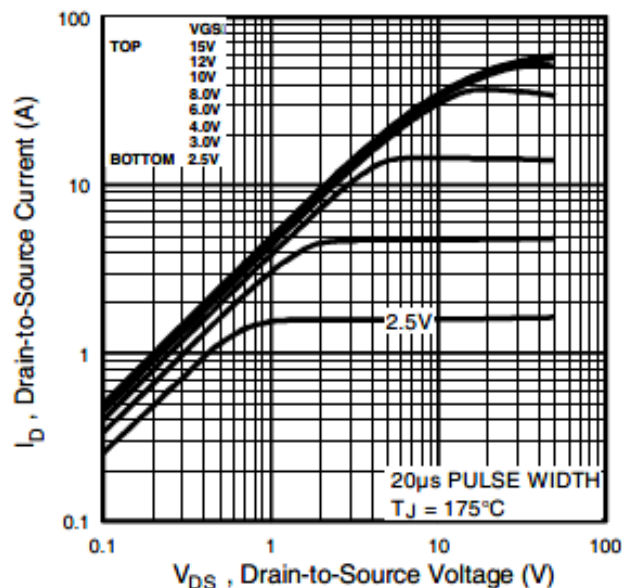


Fig. 2 Typical Output Characteristics

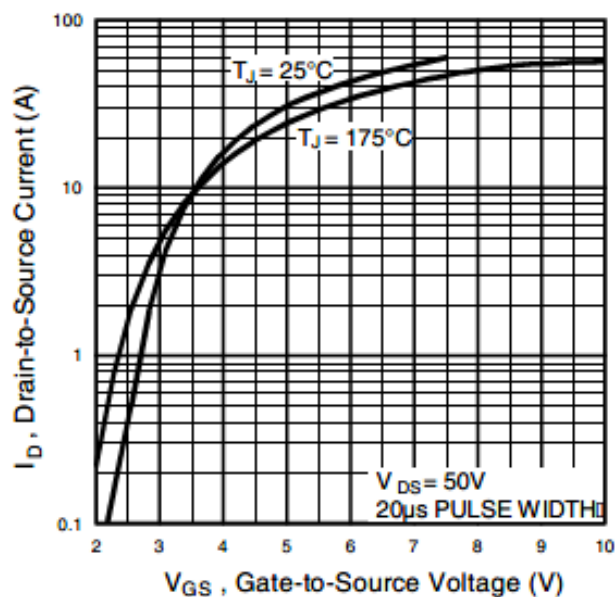


Fig. 3 Typical Transfer Characteristics

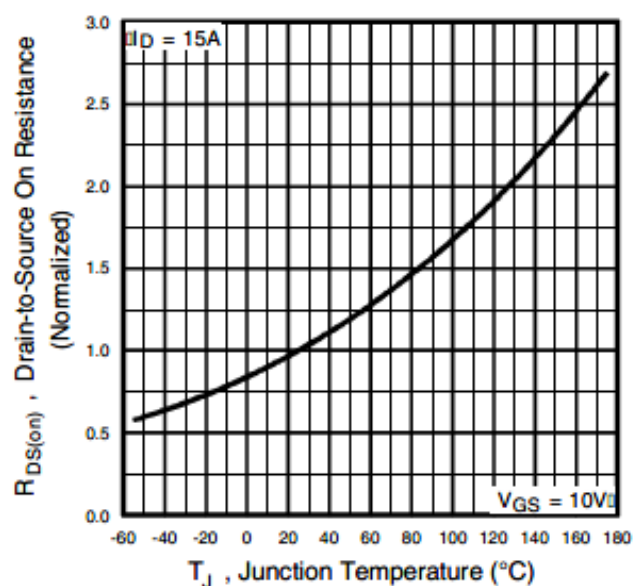


Fig. 4 Normalized On-Resistance vs. Temperature

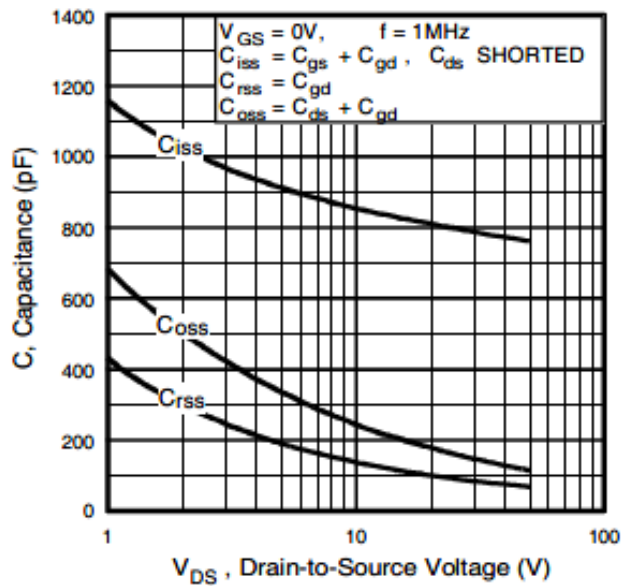


Fig 5. Typical Capacitance vs.
Drain-to-Source Voltage

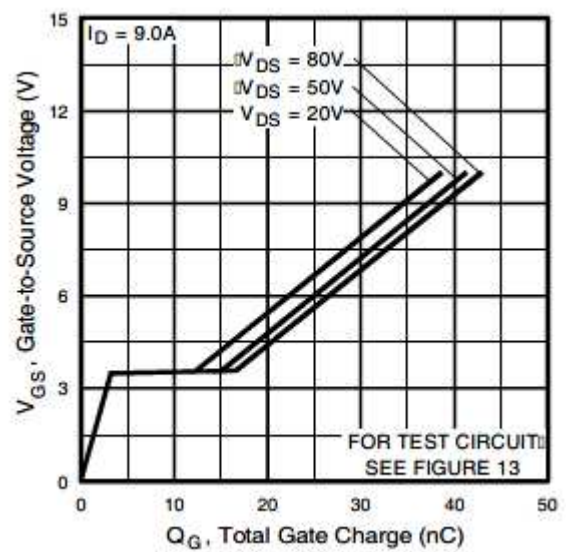


Fig 6. Typical Gate Charge vs.
Gate-to-Source Voltage

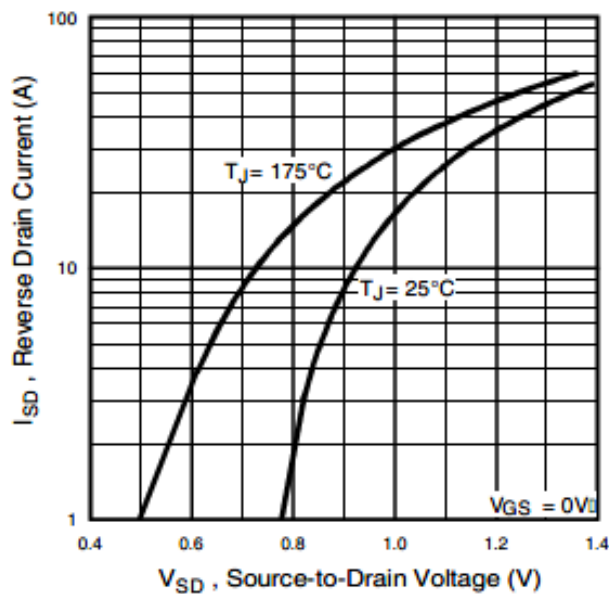


Fig. 7 Typical Source-to-Drain Diode
Forward Voltage

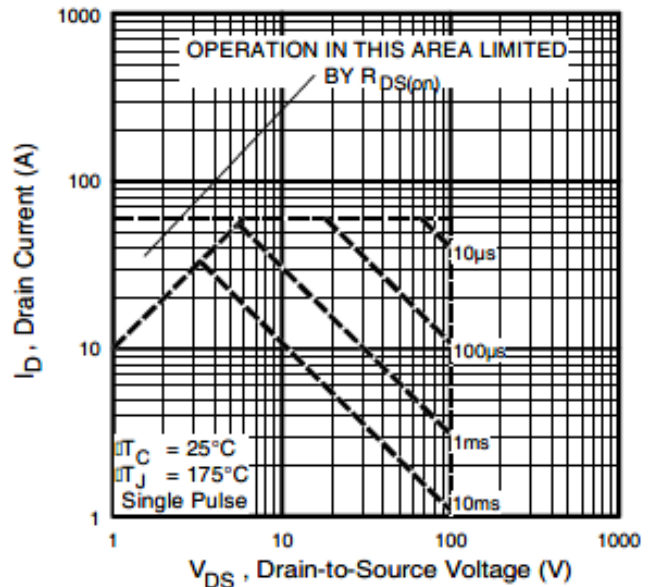


Fig 8. Maximum Safe Operating Area

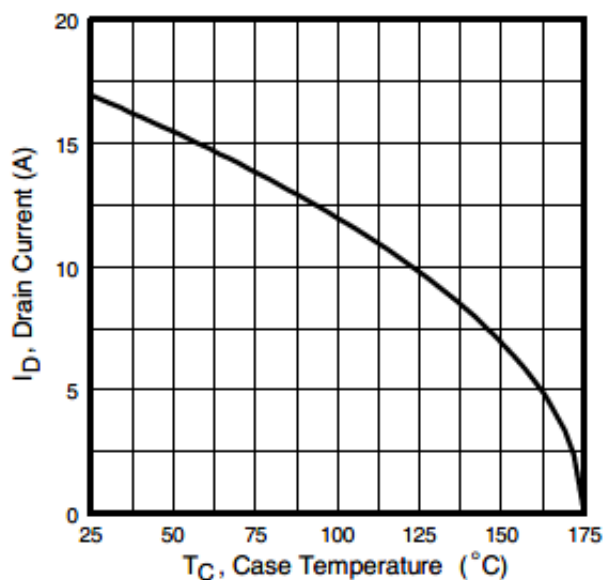


Fig 9. Maximum Drain Current vs. Case Temperature

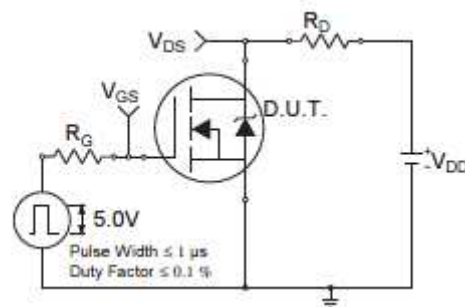


Fig 10a. Switching Time Test Circuit

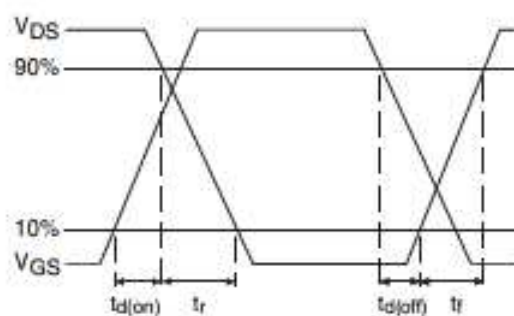


Fig 10b. Switching Time Waveforms

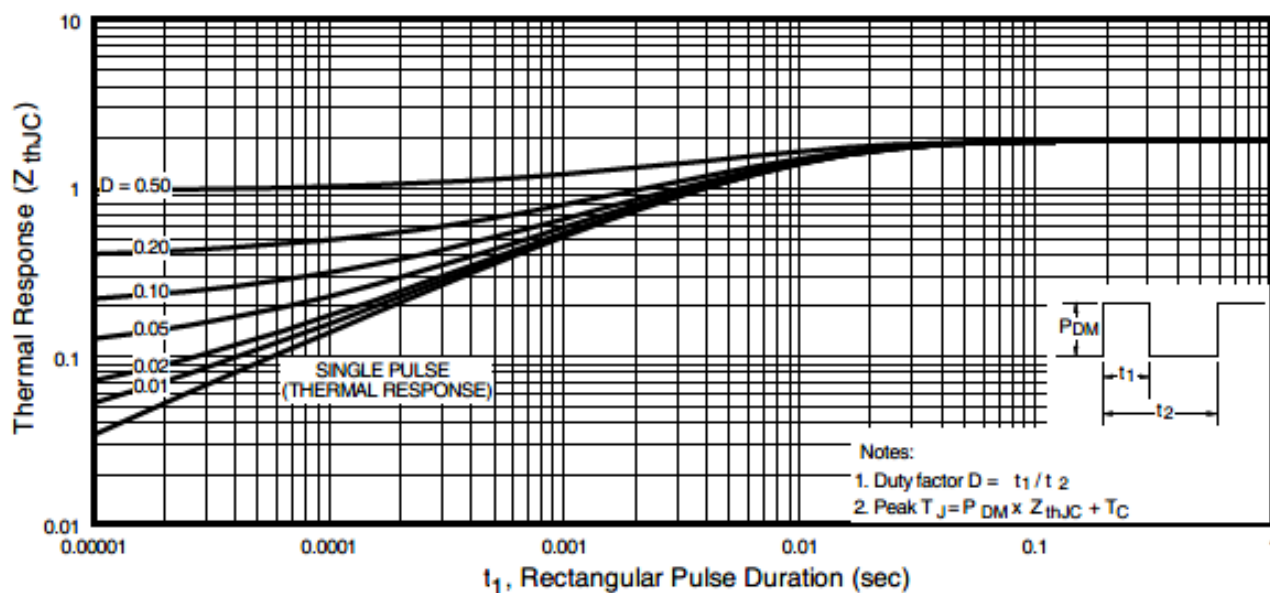


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

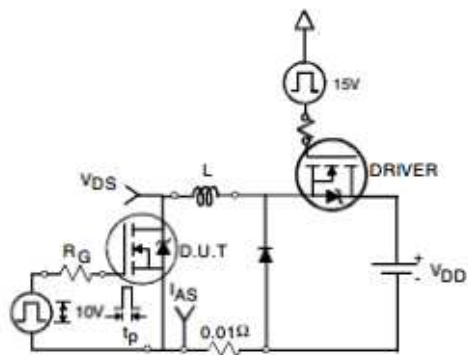


Fig 12a. Unclamped Inductive Test Circuit

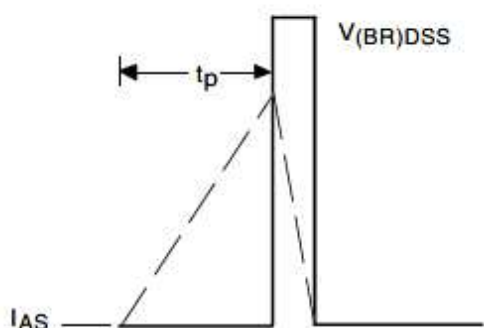


Fig 12b. Unclamped Inductive Waveforms

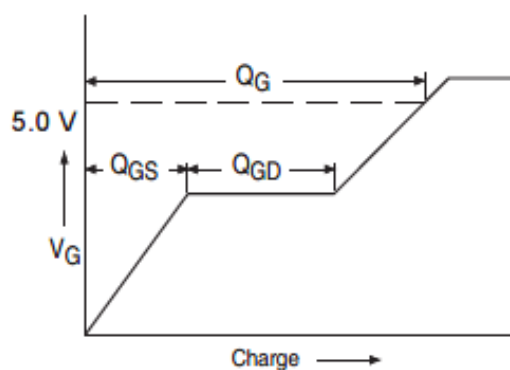


Fig 13a. Gate Charge Waveform

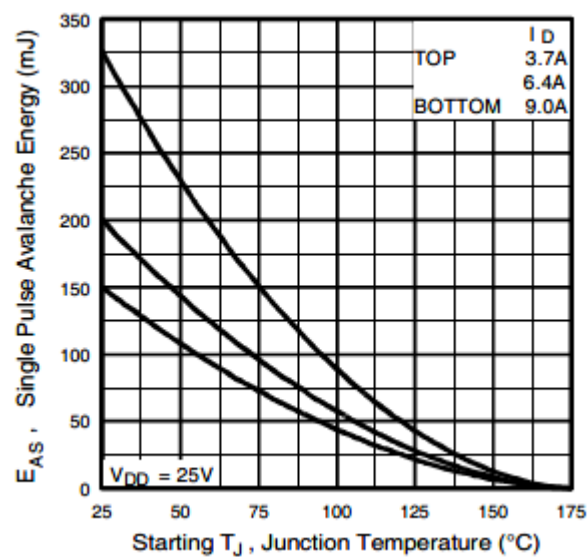


Fig 12c. Maximum Avalanche Energy vs. Drain Current

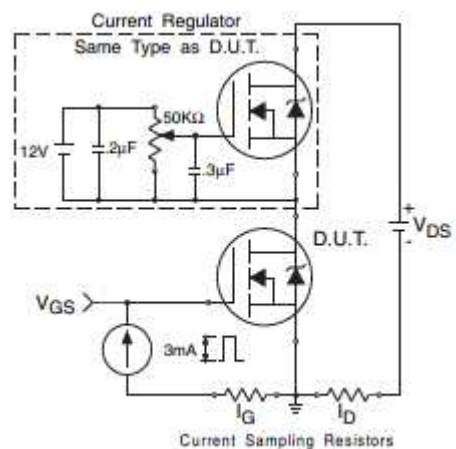


Fig 13b. Gate Charge Test Circuit

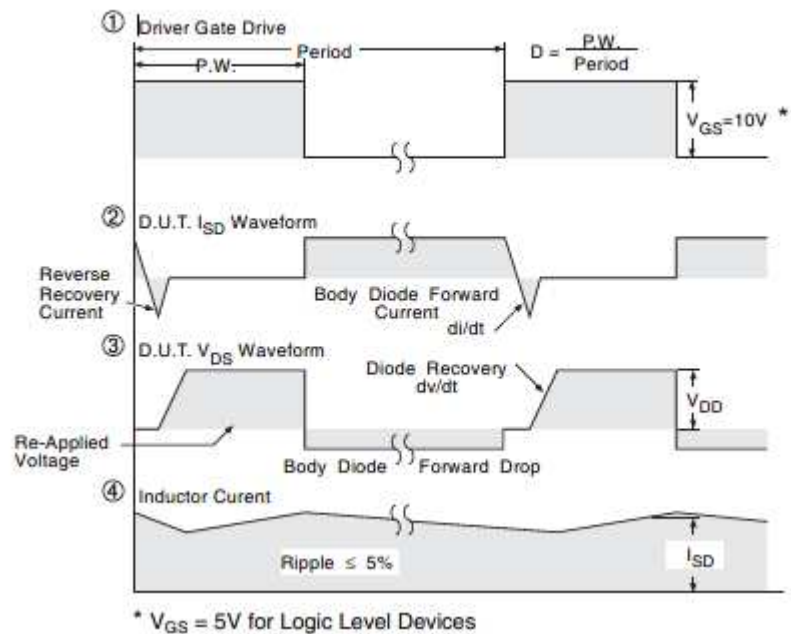
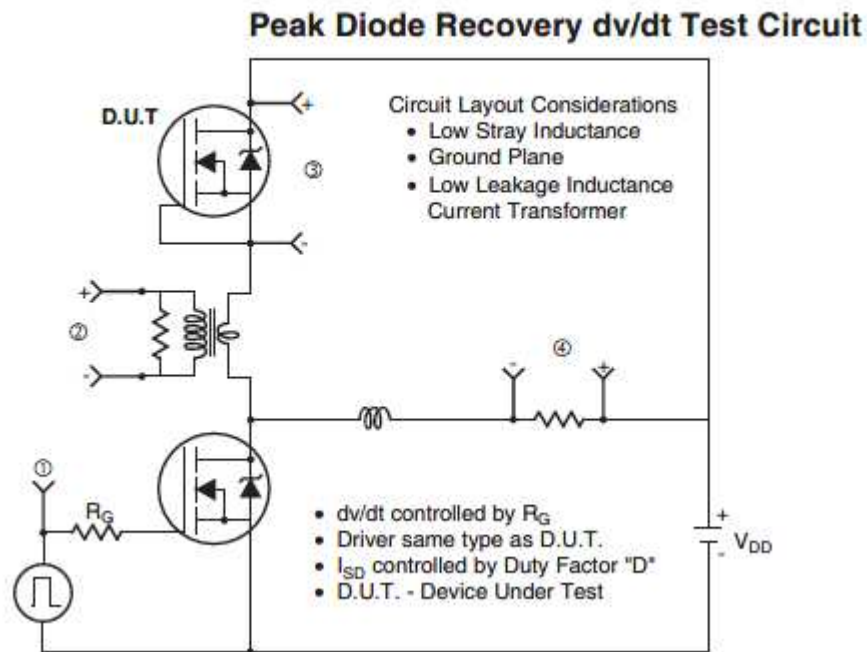
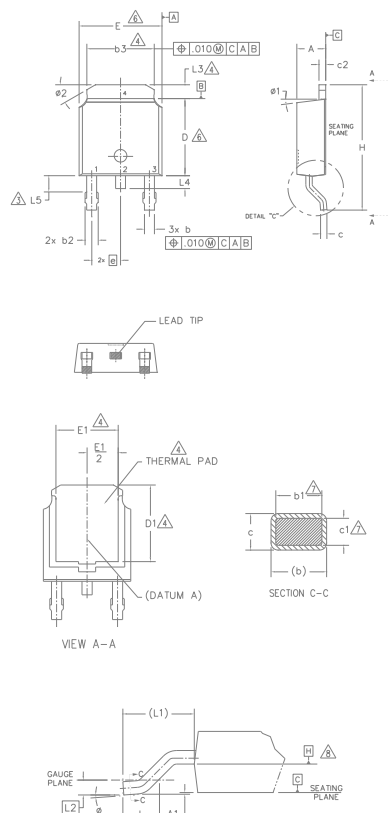


Fig 14. Peak Diode Recovery dv/dt Test Circuit for N-Channel HEXFET® Power MOSFETs

D-Pak (TO-252AA) Package Outline (Dimensions are shown in millimeters (inches))



NOTES:

- 1.- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-1994
- 2.- DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
- 3.- LEAD DIMENSION UNCONTROLLED IN L5.
- 4.- DIMENSION D1, E1, L3 & b3 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
- 5.- SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 AND 0.10 [0.13 AND 0.25] FROM THE LEAD TIP.
- 6.- DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .006 [0.15] PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTMOST EXTREMES OF THE PLASTIC BODY.
- 7.- DIMENSION b1 & c1 APPLIED TO BASE METAL ONLY.
- 8.- DATUM A & B TO BE DETERMINED AT DATUM PLANE H.
- 9.- OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	DIMENSIONS				NOTES
	MILLIMETERS		INCHES		
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	7
A1	—	0.13	—	.005	
b	0.64	0.89	.025	.035	
b1	0.64	0.79	.025	.031	4
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	7
c	0.46	0.61	.018	.024	
c1	0.41	0.56	.016	.022	
c2	0.46	0.89	.018	.035	6
D	5.97	6.22	.235	.245	
D1	5.21	—	.205	—	4
E	6.35	6.73	.250	.265	
E1	4.32	—	.170	—	4
e	2.29 BSC		.090 BSC		
H	9.40	10.41	.370	.410	4
L	1.40	1.78	.055	.070	
L1	2.74 BSC		.108 REF.		
L2	0.51 BSC		.020 BSC		3
L3	0.89	1.27	.035	.050	
L4	—	1.02	—	.040	
L5	1.14	1.52	.045	.060	3
ø	0"	10"	0"	10"	
ø1	0"	15"	0"	15"	
ø2	25"	35"	25"	35"	

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBT & CoPAK

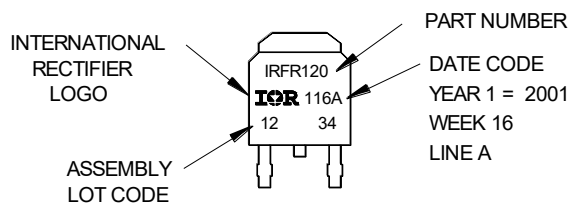
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

D-Pak (TO-252AA) Part Marking Information

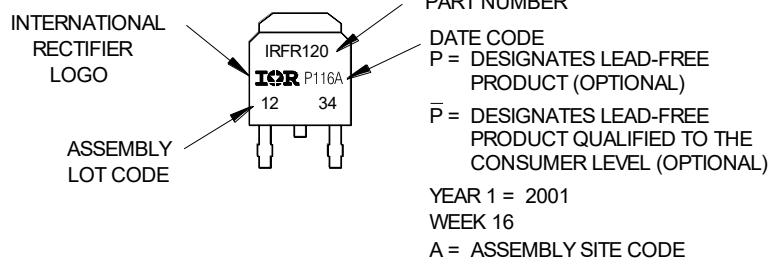
EXAMPLE: THIS IS AN IRFR120
WITH ASSEMBLY
LOT CODE 1234
ASSEMBLED ON VV 16, 2001
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position
indicates "Lead-Free"

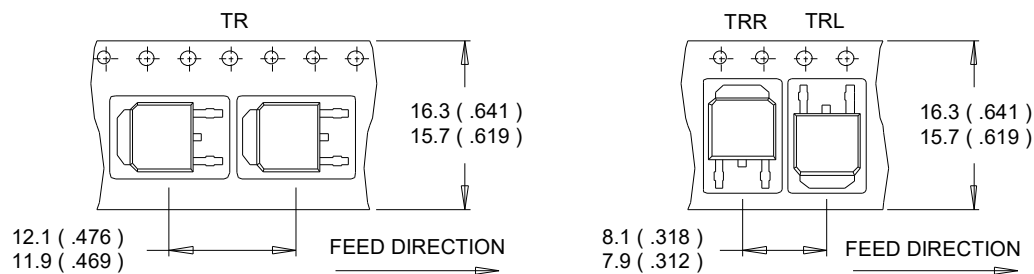
"P" in assembly line position indicates
"Lead-Free" qualification to the consumer-level



OR

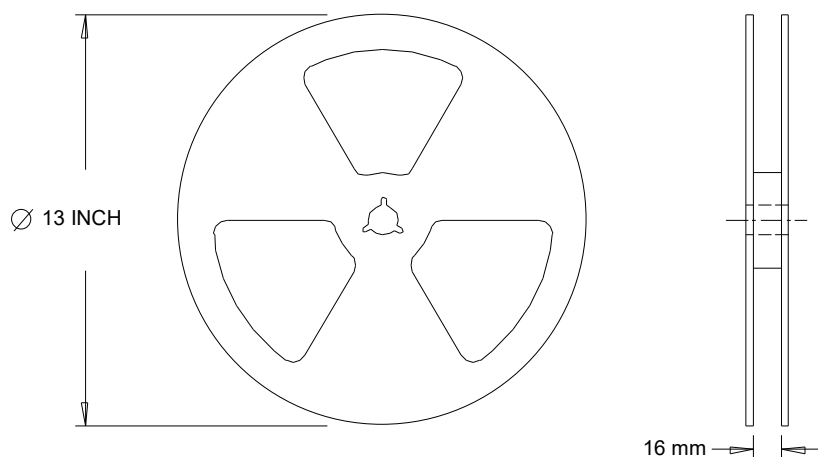


D-Pak (TO-252AA) Tape & Reel Information Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Note: For the most current drawing please refer to Infineon's web site www.infineon.com

Qualification Information[†]

Qualification Information		
Qualification Level	Industrial (per JEDEC JESD47F) ††	
Moisture Sensitivity Level	D-Pak	MSL1 (per JEDEC J-STD-020D) ††
	I-Pak	
RoHS Compliant	Yes	

† Qualification standards can be found at Infineon's web site www.infineon.com

†† Applicable version of JEDEC standard at the time of product release.

Revision History

Date	Rev.	Comments
2004-07-12	2.0	Final data sheet
2024-08-30	2.1	- Update datasheet to Infineon format - Updated typo on Rdson unit from "W" to "Ω" on page 2 - Updated package outline and part marking on page 9 & 10. - Added disclaimer on last page.

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